

# First-principles study on defect chemistry and migration of oxide ions in ceria doped with rare-earth cations

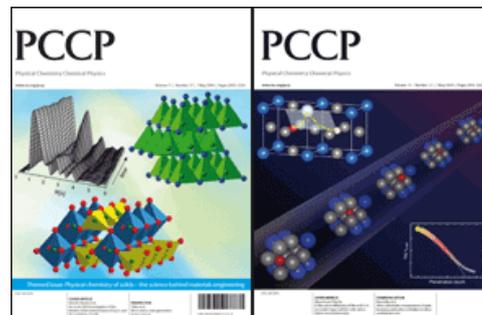
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**Communications**

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[High anion conductivity in a ternary non-equilibrium phase of BaF<sub>2</sub> and CaF<sub>2</sub> with mixed cations](#)

B. Ruprecht, M. Wilkening, A. Feldhoff, S. Steuernagel and P. Heitjans, *Phys. Chem. Chem. Phys.*, 2009

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K.-D. Becker, M. Schrader, H.-S. Kwon and H.-I. Yoo, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b823174e](https://doi.org/10.1039/b823174e)

[Oxidation states of Co and Fe in Ba<sub>1-x</sub>Sr<sub>x</sub>Co<sub>1-y</sub>Fe<sub>y</sub>O<sub>3-δ</sub> \(x, y = 0.2–0.8\) and oxygen desorption in the temperature range 300–1273 K](#)

Ashley S. Harvey, F. Jochen Litterst, Zhen Yang, Jennifer L. M. Rupp, Anna Infortuna and Ludwig J. Gauckler, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b819414a](https://doi.org/10.1039/b819414a)

[Bulk defect chemistry and surface electronic behavior of Zn,Sn codoped In<sub>2</sub>O<sub>3</sub> transparent conducting oxides](#)

Steven P. Harvey, Thomas O. Mason, Christoph Körber and Andreas Klein, *Phys. Chem. Chem. Phys.*, 2009

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[Defect chemistry of the cage compound, Ca<sub>12</sub>Al<sub>14</sub>O<sub>33</sub>—understanding the route from a solid electrolyte to a semiconductor and electride](#)

Doh-Kwon Lee, Lutz Kogel, Stefan G. Ebbinghaus, Ilia Valov, Hans-Dieter Wiemhoefer, Martin Lerch and Juergen Janek, *Phys. Chem. Chem. Phys.*, 2009

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[Electrical conductivity–defect structure correlation of variable-valence and fixed-valence acceptor-doped BaTiO<sub>3</sub> in quenched state](#)

Han-Il Yoo, Tae-Sik Oh, Hyung-Soon Kwon, Dong-Kyu Shin and Jong-Sook Lee, *Phys. Chem. Chem. Phys.*, 2009

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[An in situ XAS investigation of the kinetics of the ammonolysis of Ga<sub>2</sub>O<sub>3</sub> and the oxidation of GaN](#)

J. Brendt, D. Samuelis, T. E. Weirich and M. Martin, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b901819k](https://doi.org/10.1039/b901819k)

[In situ investigation of coloration processes in LiNbO<sub>3</sub>: MgO during reducing/oxidizing high-temperature treatments](#)

Dmytro Sugak, Yaroslav Zhydashchuk, Yuriy Sugak, Oleg Buryy, Sergii Ubizskii, Ivan Solskii, Alexander Börger and Klaus-Dieter Becker, *Phys. Chem. Chem. Phys.*, 2009

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**Voltage-assisted  $^{18}\text{O}$  tracer incorporation into oxides for obtaining shallow diffusion profiles and for measuring ionic transference numbers: basic considerations**

J. Fleig, *Phys. Chem. Chem. Phys.*, 2009

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**Oxygen incorporation into strontium titanate single crystals from  $\text{CO}_2$  dissociation**

Chr. Argirusis, F. Voigts, P. Datta, J. Grosse-Brauckmann and W. Maus-Friedrichs, *Phys. Chem. Chem. Phys.*, 2009

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**Construction of nano- and microporous frameworks from octahedral bubble clusters**

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**Bubbles and microporous frameworks of silicon carbide**

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**Band gap engineering of  $\text{ZnO}$  via doping with manganese: effect of Mn clustering**

Hilkka Saal, Thomas Bredow and Michael Binnewies, *Phys. Chem. Chem. Phys.*, 2009

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**Transport pathways for mobile ions in disordered solids from the analysis of energy-scaled bond-valence mismatch landscapes**

Stefan Adams and R. Prasada Rao, *Phys. Chem. Chem. Phys.*, 2009

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**Ultrathin oxide films and heterojunctions:  $\text{CaO}$  layers on  $\text{BaO}$  and  $\text{SrO}$**

Chris E. Mohn, Neil L. Allan and John H. Harding, *Phys. Chem. Chem. Phys.*, 2009

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**Formation entropies of intrinsic point defects in cubic  $\text{In}_2\text{O}_3$  from first-principles density functional theory calculations**

Péter Ágoston and Karsten Albe, *Phys. Chem. Chem. Phys.*, 2009

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**Hydrogen adsorption on Pd-containing  $\text{Au}(111)$  bimetallic surfaces**

Sudha Venkatachalam and Timo Jacob, *Phys. Chem. Chem. Phys.*, 2009

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**Interdiffusion and surface-sandwich ordering in initial Ni-core-Pd-shell nanoparticle**

Alexander V. Evteev, Elena V. Levchenko, Irina V. Belova and Graeme E. Murch, *Phys. Chem. Chem. Phys.*, 2009

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**First-principles study on defect chemistry and migration of oxide ions in ceria doped with rare-earth cations**

Masanobu Nakayama and Manfred Martin, *Phys. Chem. Chem. Phys.*, 2009

**DOI: [10.1039/b900162j](https://doi.org/10.1039/b900162j) An electrochemical study of lithium insertion into  $\text{Cr}_x\text{Ti}_y\text{Se}_z$  ( $x, y, z = 1, 2, 3, 4, 4.5$ ) beyond the intercalation limit**

Sylvio Indris, Joseph Wontcheu and Wolfgang Bensch, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b822397a](https://doi.org/10.1039/b822397a)

**Mixed  $\text{LiCo}_x\text{M}_{0.4}\text{PO}_4$  ( $M = \text{Mn, Fe, Ni}$ ) phosphates: cycling mechanism and thermal stability**

Natalia N. Bramnik, Dmytro M. Trots, Heiko J. Hofmann and Helmut Ehrenberg, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b901319a](https://doi.org/10.1039/b901319a)

**Changes in the crystal and electronic structure of  $\text{LiCoO}_2$  and  $\text{LiNiO}_2$  upon Li intercalation and de-intercalation**

Sonja Laubach, Stefan Laubach, Peter C. Schmidt, David Ensling, Stefan Schmid, Wolfram Jaegermann, Andreas Thißen, Kristian Nikolowski and Helmut Ehrenberg, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b901200a](https://doi.org/10.1039/b901200a)

**Partial oxidation of methanol on well-ordered  $\text{V}_2\text{O}_5(001)/\text{Au}(111)$  thin films**

J. M. Sturm, D. Göbke, H. Kühlenbeck, J. Döbler, U. Reinhardt, M. V. Ganduglia-Pirovano, J. Sauer and H.-J. Freund, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b822384j](https://doi.org/10.1039/b822384j)

**Investigation of the nucleation and growth dynamics of FePt nanoparticles prepared via a high-temperature synthesis route employing  $\text{PtCl}_4$  as platinum precursor**

Hauke Heller, Kirsten Ahrenstorf, Jose A. C. Broekaert and Horst Weller, *Phys. Chem. Chem. Phys.*, 2009

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**Non-oxidic nanoscale composites: single-crystalline titanium carbide nanocubes in hierarchical porous carbon monoliths**

Kirstin Sonnenburg, Bernd M. Smarsly and Torsten Brezesinski, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b822437d](https://doi.org/10.1039/b822437d)

**Poly(*p*-phenylene sulfone)s with high ion exchange capacity: ionomers with unique microstructural and transport features**

C. C. de Araujo, K. D. Kreuer, M. Schuster, G. Portale, H. Mendil-Jakani, G. Gebel and J. Maier, *Phys. Chem. Chem. Phys.*, 2009

DOI: [10.1039/b822069g](https://doi.org/10.1039/b822069g)

**Pulsed electrodeposition of porous  $\text{ZnO}$  on Ag-coated polyamide filaments**

Melanie Rudolph, Thomas Loewenstein, Elisa Arndt, Yvonne Zimmermann, Andreas Neudeck and Derck Schlettwein, *Phys. Chem. Chem. Phys.*, 2009

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# First-principles study on defect chemistry and migration of oxide ions in ceria doped with rare-earth cations

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Oxygen transport in rare-earth oxide (RE<sub>2</sub>O<sub>3</sub>) doped CeO<sub>2</sub> with fluorite structure has attracted considerable attention owing to both the range of practical usage (*e.g.*, fuel cells, sensors, *etc.*) and the fundamental fascination of fast oxide ion transport in crystalline solids. Using density-functional theory, we have calculated the formation energies of point defects and their migration properties in RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> (RE = Sc, Y, La, Nd, Sm, Gd, Dy, and Lu). The calculated results show that oxygen vacancies are the dominant defect species obtained by RE<sup>3+</sup> doping. They form associates with the RE<sup>3+</sup> ions, and the corresponding defect association energy is a strong function of the ionic radii of the RE<sup>3+</sup> dopants. The migration of an oxygen vacancy was investigated using the nudged elastic band method. The lowest activation energy for oxygen vacancy hopping is obtained for a straightforward migration path between two adjacent oxygen sites. The migration energy of an oxygen vacancy also strongly depends on the ionic radii of the neighbouring dopant cations. Accordingly, we have identified two factors that affect the oxygen vacancy migration; (1) trapping (or repelling) of an oxygen vacancy at the NN site of the RE<sup>3+</sup> dopant, and (2) reduction (or enlargement) of the migration barrier by RE<sup>3+</sup> doping. These findings provide insight for atomistic level understanding of ionic conductivity in doped ceria and would be beneficial for optimizing ionic conductivity.

## 1. Introduction

Oxide ion transport in ceria (CeO<sub>2</sub>) based materials with a fluorite structure is of great interest in the development of electrolytes for solid oxide fuel cells due to its high ionic conductivity.<sup>1,2</sup> Pure CeO<sub>2</sub> itself is not a good ionic conductor, but a significant increase in conductivity can be achieved by rare-earth oxide (RE<sub>2</sub>O<sub>3</sub>; RE denotes a rare-earth element) doping due to creation of oxygen vacancies. Therefore, RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> materials have been studied extensively for many years by measuring the oxide ion conductivities and their activation energies as functions of the dopant concentration and/or the temperature.<sup>3,4</sup> The results showed a strong dependence of the conductivity on the ionic radius of the dopants. The maximum conductivity was observed in CeO<sub>2</sub> doped with Sm<sub>2</sub>O<sub>3</sub> while replacement of Ce<sup>4+</sup> by larger or smaller RE<sup>3+</sup> ions than Sm<sup>3+</sup> caused a decrease in ionic conduction.<sup>4</sup> The effect is believed to be due to the local structure driven properties, such as local distortion or lattice strain owing to the size mismatch between host Ce<sup>4+</sup> ions and dopant RE<sup>3+</sup> ions, and the trapping effect of the oxygen vacancies by the dopant ions. For example, Gerhardt-Anderson *et al.* suggested that trapping effects stem from the formation of a (RE<sub>Ce</sub><sup>+</sup> V<sub>O</sub><sup>••</sup>) cluster on nearest neighbour (NN) or on next nearest-neighbor (NNN) positions.<sup>3</sup> Based on this idea, they estimated the defect association enthalpies from conductivity

measurements. Smaller size ions (*e.g.* Sc<sup>3+</sup>) among the series of RE dopants resulted in strong association, and *vice versa*. These results are qualitatively reproduced by computations using a Born-like empirical potential model.<sup>5</sup> Similarly, Zacate *et al.* reported for doped ZrO<sub>2</sub> (fluorite structure) that the defect association enthalpy (or binding energy) between a dopant RE<sup>3+</sup> ion and a nearest neighbour (NN) oxygen vacancy decreases with decrease of the ionic radius of the RE<sup>3+</sup> ions.<sup>6</sup> Very recently, Wei *et al.* calculated the defect association energy in CeO<sub>2</sub> doped with 9 types of rare-earth oxides using also an empirical potential model.<sup>7</sup> A clear tendency was found that small dopants attract an oxygen vacancy, while strong association occurs between Ce<sup>4+</sup> and an oxygen vacancy for large dopants. An EXAFS study of RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> reported by Yoshida *et al.* confirmed that oxygen vacancies tend to be associated with RE<sup>3+</sup> dopants.<sup>8</sup> On the other hand, molecular-dynamics (MD) simulations using empirical potentials in yttria-stabilized ZrO<sub>2</sub> revealed that the difference in conductivity at different dopant concentrations is not caused by defect association between oxygen vacancies and the Y<sup>3+</sup> dopant but rather due to the strongly reduced hopping probabilities of oxygen ions around Y<sup>3+</sup> dopant ions.<sup>9</sup> However, the computational approaches using Born-like potential model in the above studies<sup>5-7,9</sup> may suffer from the precise assignments of potential parameters due to the increase of the number of parameters with increasing number of dopant species. In this respect, the first-principles DFT approach is advantageous due to the absence of adjustable (empirical) parameters in its formalism. Yoshida *et al.* studied the migration energy of Y, La and Sm doped ceria<sup>10</sup> and suggested a relationship between the ionic

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conductivity and the lattice deformation. Andersson *et al.* reported recently a first-principles DFT study on dopant-oxygen vacancy interaction, or the defect association energy and the migration barrier, in CeO<sub>2</sub> doped with various rare earth oxides.<sup>11</sup> They showed a clear relationship between the defect interactions and the atomic number (or ionic radius) of the RE dopant, and they predicted an effective activation energy for ionic conduction. However, the computational results in<sup>10,11</sup> were derived from a few specific RE/Ce/O/vacancy configurations.

Therefore, a comprehensive understanding of the energetics concerning (1) the defect chemistry and (2) the migration of oxygen vacancies is required to clarify the effect of different RE<sup>3+</sup> dopants and different local configurations on oxygen transport in RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub>. In this paper, first-principles density functional theory (DFT) is adopted to reveal the influence of the above two factors in CeO<sub>2</sub> doped with eight different RE<sub>2</sub>O<sub>3</sub>. As rare earth element Sc, Y, La, Nd, Sm, Gd, Dy, and Lu were chosen to cover a wide range of ionic radii from ~1.0 to ~1.3 Å. In addition, several atomic configurations were considered to understand comprehensively the effects of local atomic arrangements for defect association and migration barriers.

The first-principles DFT approach will give us an atomistic level understanding of the macroscopic oxide ion transport phenomena, and this insight could be used for the design of materials with improved properties. For example, Murray *et al.* simulated the oxide ion conductivity in Y<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> by combining atomistic simulation methods and Monte Carlo simulations.<sup>12</sup> Krishnamurthy *et al.*<sup>13,14</sup> and Pomprasertsuk *et al.*<sup>15</sup> reported combined first-principles DFT and Monte Carlo techniques for Y<sub>2</sub>O<sub>3</sub> doped ZrO<sub>2</sub>. Thus, the aim of this paper is to gain knowledge of the energies related to defect chemistry and migration barriers which is the first step on the way to predict the ionic conductivity. In the following steps these energies must be expanded and linked to the macroscopic behaviour and properties. For example, these energies could be used directly in the above models<sup>12–15</sup> to predict the macroscopic ionic conductivity. In this respect, we will use the present computational results along with a simplified conductivity model proposed in ref. 16 to demonstrate qualitatively the dependence of the ionic conduction behaviour on the dopant fraction in Y<sub>2</sub>O<sub>3</sub> doped Ceria.

This paper is arranged as follows. Section 1 contains the introduction. Section 2 describes the details of the first-principles DFT procedure. Section 3 consists of two subsections that discuss the physical properties of pure CeO<sub>2</sub> (Sec. 3.1), and the defect chemistry of RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> (Sec. 3.2). Section 4 contains the results of oxide ion migration (or oxide ion jumps between lattice sites) in pure ceria and in RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub>. Finally, section 5 gives a summary and conclusions.

## 2. Computational methods

All first-principles DFT calculations were performed using the Vienna *ab initio* simulation package (VASP)<sup>17,18</sup> with the generalized gradient approximation (PBE-GGA)<sup>19</sup> and the projector-augmented wave (PAW) method.<sup>20</sup> (Recently, the importance for describing localized 4f states

was pointed out, such as by using the so called DFT + *U* method.<sup>21–27</sup> However, this method was not used in this study, because the major ions of Ce<sup>4+</sup> and O<sup>2–</sup> in RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> do not possess 4f electrons, and several adjustable *U* parameters for the different RE<sup>3+</sup> ions would be needed which causes similar problems as the Born-like potential model mentioned before.) Spin polarization calculation was adopted. At first, we calculated ‘perfect CeO<sub>2</sub>’ without any defects in the lattice, under the condition of full structural relaxation (*i.e.* allowing for the change of the cubic lattice parameter and the internal atomic positions). Then, the final energies of the optimized geometries were recalculated so as to correct for changes in the plane-wave basis during relaxation.

After determining the lattice parameter of pure CeO<sub>2</sub>, we expanded the simulation cell to a size of 2 × 2 × 2 conventional fluorite unit cells (Ce<sub>32</sub>O<sub>64</sub>) to model point defects, such as an oxygen vacancy, a substitutional cation, and their associates, but also the migration of oxygen ions. In all the computations, we controlled the total number of electrons in the lattice to compensate for excess charges of impurities or defects. For instance, when we assume the situation that an impurity RE atom replaces a Ce atom (*i.e.* [RECe<sub>31</sub>O<sub>64</sub>]<sup>–</sup>), one excess electron is added into the lattice. A jellium background was used to neutralize the lattice with charged point defects (oxygen vacancy and/or trivalent cations). It was also assumed that structural relaxation only affects the local surrounding of the defects in the 2 × 2 × 2 superstructure. Thus, only internal atomic positions in the cell were allowed to relax and the cubic lattice parameter was fixed for the calculations. The validity of this approach was confirmed by the fact that the energy difference of oxygen vacancy formation was less than 0.01 eV for the two simulation cells Ce<sub>32</sub>O<sub>63</sub> and Ce<sub>48</sub>O<sub>95</sub>.

The nudged elastic band (NEB) method was used to investigate the minimum energy pathways of the oxygen vacancy hopping from one lattice position to adjacent sites. First, the two point configurations (initial and end point) and the corresponding total energies were calculated by specifying the location of a vacancy at the two potential minima. In this computation, the internal atomic positions in the cell were relaxed without changing the lattice parameter, as mentioned above. Then intermediate configurations were generated by linear interpolation between the initial and end points. Finally, the intermediate configurations were relaxed under the constraint that the ions were connected by springs to keep the ions equidistant from neighbouring configurations during the relaxation. Details of the NEB method are described in ref. 28.

## 3. Results: defect chemistry

### 3.1 Perfect CeO<sub>2</sub>

Table 1 lists the obtained cubic lattice parameter and the bulk modulus for perfect CeO<sub>2</sub> as obtained by DFT computations and by experiments. The conventional fluorite structure was calculated with a Ce<sub>4</sub>O<sub>8</sub> superstructure using 5 × 5 × 5 *k*-point meshes, and the bulk modulus was obtained along with Murnaghan’s formula.<sup>29</sup> The present results show good agreement with previous studies within the typical

**Table 1** Cubic lattice parameter and bulk modulus of CeO<sub>2</sub> obtained by density functional theory (DFT) computations and experiments

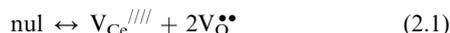
Property	Computation (DFT)	Experiments
Cubic lattice parameter/Å	5.463, <sup>a</sup> 5.45, <sup>30</sup> 5.37, <sup>31</sup> 5.48, <sup>32</sup> 5.45 <sup>33</sup>	5.41 <sup>34</sup>
Bulk modulus/GPa	181.03, <sup>a</sup> 193.5, <sup>31</sup> 187.7 <sup>32</sup>	236, <sup>35</sup> 204 <sup>36</sup>

<sup>a</sup> Present work.

DFT-GGA error. For later calculations of the defect structure and the migration of an oxygen vacancy, we used a Ce<sub>32</sub>O<sub>64</sub>-based superstructure as mentioned in the previous section. Thus, we compared the computational results for perfect CeO<sub>2</sub> using two different cell sizes, Ce<sub>4</sub>O<sub>8</sub> and Ce<sub>32</sub>O<sub>64</sub>. For Ce<sub>32</sub>O<sub>64</sub>, numerical integration over the Brillouin zone was carried out only by sampling the  $\Gamma$  point due to limitations of our computational resources. The obtained total energy difference between Ce<sub>4</sub>O<sub>8</sub> and Ce<sub>32</sub>O<sub>64</sub> is small enough (1.1 meV per CeO<sub>2</sub>) to ensure that our superstructure computations capture the physical and chemical properties with the quality presented in Table 1.

### 3.2 RE<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub>

As pointed out in many reports, oxygen vacancy formation is mandatory for oxygen ion migration in ceria (or in fluorite structured oxides in general). One important intrinsic defect formation reaction is the Schottky reaction (eqn (2.1), Kröger–Vink notation)



Another candidate for oxygen vacancy creation is the Anti-Frenkel reaction (eqn (2.2))



Here, we assume the interstitial sites for oxygen (O<sub>i</sub><sup>II</sup>) to be the 4b Wyckoff positions of the space group *Fm* $\bar{3}$ *m*, or the large cavities at the centre of the fluorite structure. To calculate the defect formation energy for both reactions, we consider dilute conditions where the created point defects do not interact with each other. Thus, we can calculate the total energy  $E_{\text{tot}}(\text{N}_{\text{Ce}}, \text{N}_{\text{O}})$  of a system that contains a single point defect in the supercell Ce<sub>32</sub>O<sub>64</sub> separately, and then we can sum up the terms to obtain the reactions in the above eqns (2.1) and (2.2). The corresponding defect formation energies  $E_{\text{def}}^{\text{S}}$  (Schottky defect) and  $E_{\text{def}}^{\text{AF}}$  (Anti-Frenkel defect) are:

$$E_{\text{def}}^{\text{S}} = E_{\text{tot}}([\text{Ce}_{31}\text{V}_{\text{Ce}}\text{O}_{64}]^{4-}) + 2 E_{\text{tot}}([\text{Ce}_{32}\text{O}_{63}\text{V}_{\text{O}}]^{2+}) - 95 E_{\text{tot}}([\text{CeO}_2]) \quad (2.3)$$

$$E_{\text{def}}^{\text{AF}} = E_{\text{tot}}([\text{Ce}_{32}\text{O}_{64}\text{O}_i]^{2-}) + E_{\text{tot}}([\text{Ce}_{32}\text{O}_{63}\text{V}_{\text{O}}]^{2+}) - 64 E_{\text{tot}}([\text{CeO}_2]) \quad (2.4)$$

Here V<sub>Ce</sub>, V<sub>O</sub> and O<sub>i</sub> indicate a cerium vacancy, an oxygen vacancy and an oxygen interstitial ion, respectively. The results are shown in the Table 2. For comparison, the Frenkel reaction

**Table 2** Defect formation energies of intrinsic defects and fractions at 1000 K in pure ceria

Defect formation reaction	Law of mass action and calculated defect formation energy	Fraction of defects in CeO <sub>2</sub> at 1000 K
Schottky (eqn (2.1))	$K_{\text{S}} = [\text{V}_{\text{Ce}}^{\text{IV}}][\text{V}_{\text{O}}^{\bullet\bullet}]^2$ , 3.59 eV	$[\text{V}_{\text{O}}^{\bullet\bullet}] = 2[\text{V}_{\text{Ce}}^{\text{IV}}]$ $= 1.2 \times 10^{-6}$
Anti-Frenkel (eqn (2.2))	$K_{\text{AF}} = [\text{O}_i^{\text{II}}][\text{V}_{\text{O}}^{\bullet\bullet}]$ , 4.04 eV	$[\text{O}_i^{\text{II}}] = [\text{V}_{\text{O}}^{\bullet\bullet}]$ $= 6.7 \times 10^{-11}$
Frenkel (eqn (2.5))	$K_{\text{F}} = [\text{Ce}_i^{\bullet\bullet\bullet\bullet}][\text{V}_{\text{Ce}}^{\text{IV}}]$ , 7.36 eV	$[\text{Ce}_i^{\bullet\bullet\bullet\bullet}] = [\text{V}_{\text{Ce}}^{\text{IV}}]$ $= 2.8 \times 10^{-19}$

was also considered. As can be seen in Table 2, the formation of Frenkel defects requires a relatively high formation energy in comparison to the Schottky and Anti-Frenkel reactions. The equilibrium constants  $K$  of the corresponding defect formation reactions (2.1), (2.2) and (2.5) were also calculated for comparison purposes. Since statistical mechanics postulates that the fraction of defects follows the Boltzmann factor at equilibrium, then the equilibrium constant  $K$  was obtained as follows,

$$K = \exp(-E_{\text{def}}/k_{\text{B}}T) \quad (2.6)$$

where  $k_{\text{B}}$  and  $T$  are the Boltzmann constant and the absolute temperature, respectively. (Note that the Gibbs energy should be used instead of the defect formation energy to calculate the equilibrium constant.<sup>37</sup> However, we assumed the difference arising from the entropy (mainly due to vibrational one) and the volume change to be small enough for defect formation in solid state phases.) The results for the corresponding defect fractions are also listed in Table 2 and indicate quite small fractions of intrinsic defects in pure ceria.

Therefore, the main origin of oxygen vacancy creation can be ascribed to an extrinsic mechanism of doping CeO<sub>2</sub> with RE<sub>2</sub>O<sub>3</sub> resulting in Ce<sub>1-x</sub>RE<sub>x</sub>O<sub>2-x/2</sub>. The formation of oxygen vacancies can be described as



On the other hand, another defect formation mechanism is also conceivable where an interstitial site is occupied by RE<sup>3+</sup>.



In order to understand the defect chemistry on an atomistic level, we calculated the solution energy for Y<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> as a typical representative. The computation was carried out assuming dilute conditions as mentioned before. Table 3 presents the calculated solution energies per Y<sub>2</sub>O<sub>3</sub>. The results indicate that the majority point defects compensating Y'<sub>Ce</sub> are oxygen vacancies and not yttrium interstitials due to the much smaller solution energy of eqn (2.7) compared to eqn (2.8). Both obtained energies are positive, indicating that Y<sub>2</sub>O<sub>3</sub> is

**Table 3** Solution energies for the solution of Y<sub>2</sub>O<sub>3</sub> in CeO<sub>2</sub> according to different solution reactions

Defect type (eqn. #)	Solution energy/eV per Y <sub>2</sub> O <sub>3</sub>
Oxygen vacancy mechanism (eqn (2.7))	0.98
RE <sup>3+</sup> interstitial mechanism (eqn (2.8))	2.61

not soluble in  $\text{CeO}_2$  at low temperatures, while experimental studies clearly showed that  $\text{RE}_2\text{O}_3$  and  $\text{CeO}_2$  form a solid-solution up to a certain  $\text{RE}^{3+}$  concentration (see *e.g.* ref. 2). Similar results of positive solution energies were obtained for  $\text{RE}_2\text{O}_3$  doped  $\text{ZrO}_2$  using the classical potential model.<sup>6</sup> Probably, the solution Gibbs energy becomes negative by increasing the temperature due to the entropy effect and, in addition, the enthalpy may change with temperature (the synthesis is usually performed at temperatures above 1273 K). In addition, defect association, such as formation of  $\text{Y}^{3+}$ -oxygen vacancy pairs, decreases the solution energy as mentioned later. Thus, we regard oxygen vacancies (formed *via* eqn (2.1) for undoped ceria and *via* eqn (2.7) for  $\text{RE}_2\text{O}_3$  doped ceria) as dominant conduction species.

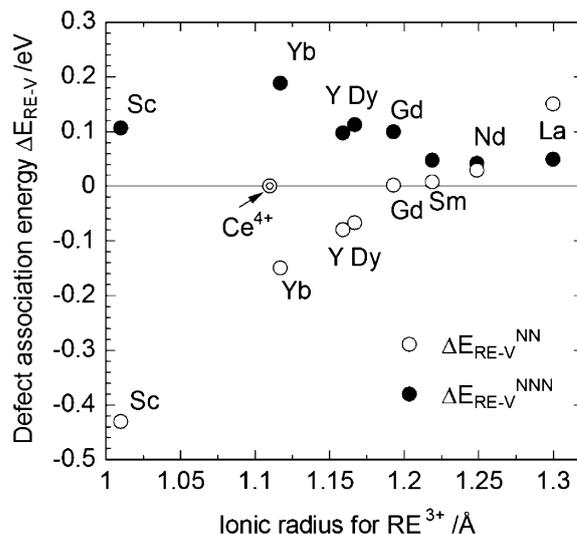
Up to now, we discussed the defect formation mechanism from the viewpoint of infinitely diluted defects, *i.e.* we assumed that defects do not interact with each other. Now, we consider in addition two types of defect associates: (1) an associate of two oxygen vacancies, ( $\text{V}_{\text{O}}^{\bullet\bullet}-\text{V}_{\text{O}}^{\bullet\bullet}$ ), and (2) an associate of an oxygen vacancy and a  $\text{RE}^{3+}$  dopant, ( $\text{RE}_{\text{Ce}}^{\prime}-\text{V}_{\text{O}}^{\bullet\bullet}$ ). For the associate ( $\text{V}_{\text{O}}^{\bullet\bullet}-\text{V}_{\text{O}}^{\bullet\bullet}$ ) we expect repulsive Coulombic interaction between the doubly charged oxygen vacancies, while we expect an attractive Coulombic interaction for the associate ( $\text{RE}_{\text{Ce}}^{\prime}-\text{V}_{\text{O}}^{\bullet\bullet}$ ) due to the opposite charges of the rare earth dopant and the oxygen vacancy. Both associates would cause a decrease of the oxygen ion conductivity due to a correlated motion of oxygen vacancies repelling each other and due to trapping of oxygen vacancies by  $\text{RE}^{3+}$ . In fact, defect association between an oxygen vacancy and a  $\text{RE}^{3+}$ -dopant was already found in fluorite-structured materials by means of atomistic simulations<sup>5</sup> and/or in experiments.<sup>3</sup> Thus, we evaluated the two defect association effects quantitatively by calculating the corresponding defect association energies  $\Delta E_{\text{V-V}}$  and  $\Delta E_{\text{RE-V}}$  as follows,

$$\begin{aligned}\Delta E_{\text{V-V}} &= [E_{\text{tot}}(\text{V}_{\text{O}}^{\bullet\bullet}-\text{V}_{\text{O}}^{\bullet\bullet})] - [2E_{\text{tot}}(\text{V}_{\text{O}}^{\bullet\bullet})] \\ &= [E_{\text{tot}}([\text{Ce}_{31}\text{O}_{62}]^+) + 32E_{\text{tot}}([\text{CeO}_2])] \\ &\quad - [2E_{\text{tot}}([\text{Ce}_{32}\text{O}_{63}]^{2+})] \quad (2.9)\end{aligned}$$

$$\begin{aligned}\Delta E_{\text{RE-V}} &= [E_{\text{tot}}(\text{RE}_{\text{Ce}}^{\prime}-\text{V}_{\text{O}}^{\bullet\bullet})] - [E_{\text{tot}}(\text{RE}_{\text{Ce}}^{\prime}) + E_{\text{tot}}(\text{V}_{\text{O}}^{\bullet\bullet})] \\ &= [E_{\text{tot}}([\text{RECe}_{31}\text{O}_{63}]^+) + 32E_{\text{tot}}([\text{CeO}_2])] \\ &\quad - [E_{\text{tot}}([\text{RECe}_{31}\text{O}_{64}]^-) + E_{\text{tot}}([\text{Ce}_{32}\text{O}_{63}]^{2+})] \quad (2.10)\end{aligned}$$

where  $E_{\text{tot}}(\text{X})$  indicates the total energy of X. In both equations, the first and the second square-bracketed terms correspond to the total energies of associated defects and isolated defects, respectively. Note that a negative defect association energy  $\Delta E_{\text{RE-V}}$  is often referred to as binding energy.

The calculated result for the defect association energy of two oxygen vacancies (eqn (2.9)) is  $\Delta E_{\text{V-V}} \sim +0.77$  eV, *i.e.* the formation of two isolated oxygen vacancies is energetically more stable than the formation of the oxygen vacancy pair, ( $\text{V}_{\text{O}}^{\bullet\bullet}-\text{V}_{\text{O}}^{\bullet\bullet}$ ). Despite the large energy penalty for formation of ( $\text{V}_{\text{O}}^{\bullet\bullet}-\text{V}_{\text{O}}^{\bullet\bullet}$ ), this defect association will become important when the conductivity is considered, because in the conductivity one needs to consider at least the oxygen vacancy distribution in

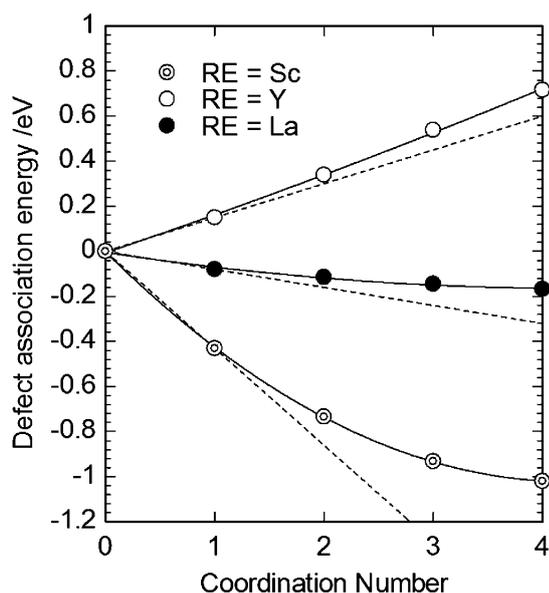


**Fig. 1** Calculated defect association energies  $\Delta E_{\text{RE-V}}^{\text{NN}}$  and  $\Delta E_{\text{RE-V}}^{\text{NNN}}$  between a  $\text{RE}^{3+}$  dopant and an oxygen vacancy located on NN and NNN sites.

NNN sites (12 sites in  $\text{CeO}_2$ ) that affects oxygen vacancy jumps to NN sites (6 sites in  $\text{CeO}_2$ ).

The defect association energies of a  $\text{RE}^{3+}$ -dopant and an oxygen vacancy on nearest neighbour sites,  $\Delta E_{\text{RE-V}}^{\text{NN}}$  and next-nearest neighbour sites,  $\Delta E_{\text{RE-V}}^{\text{NNN}}$ , are plotted in Fig. 1 as a function of the ionic radii using eqn (2.10). (The ionic radii of  $\text{RE}^{3+}$  ions are referred to in Shannon's report.<sup>38</sup>) The NN association energy increases in a linear manner with the ionic radius of the dopants from  $-0.45$  eV to  $+0.15$  eV, whereas the NNN association energy is always positive and decreases slightly from  $\sim 0.05$  to  $\sim 0.20$  eV.<sup>39</sup> For NN interaction, the sign of the defect association energy changes from negative to positive by introducing  $\text{RE}^{3+}$ -dopants with ionic radii larger than  $\sim 1.2$  Å (or larger than  $\text{Gd}^{3+}$ ). In other words, dopants with smaller ionic radii than  $\text{Gd}^{3+}$  trap an oxygen vacancy at the NN site, while larger dopants repel it. The defect association energy is a strong function of the ionic size of the dopant  $\text{RE}^{3+}$ , showing that structural distortions around defects contribute to stabilization or destabilization of defect association. It is noted that the ionic radius corresponding to  $\Delta E_{\text{RE-V}}^{\text{NN}} = 0$  differs from the ionic radius of  $\text{Ce}^{4+}$  (the ionic radius of  $\text{Ce}^{4+}$  is  $\sim 1.11$  Å<sup>38</sup>). This indicates that local structural modifications induced by dopants of different size compared to the host  $\text{Ce}^{4+}$  ions would not be the only factor to account for the defect association energy. One of the possible reasons is the difference of the valence states of  $\text{RE}^{3+}$  and  $\text{Ce}^{4+}$ .

To further investigate defect association between a  $\text{RE}^{3+}$  dopant and an oxygen vacancy, the variation of the defect association energy as a function of the coordination number (CN) of a vacancy with  $\text{RE}^{3+}$  ( $\text{RE} = \text{Sc}, \text{Y}, \text{La}$ ) ions was calculated and is plotted in Fig. 2. In this figure, an isolated oxygen vacancy that is surrounded by a single or plural NN  $\text{RE}^{3+}$  ions is considered (CN = 0 corresponds to an oxygen vacancy in pure Ceria). The hatched lines in Fig. 2 indicate the linear extrapolation of the defect association energies for CN = 0 and CN = 1. Hence, these hatched lines correspond



**Fig. 2** Variation of the defect association energy  $\Delta E_{RE-V}^{NN}$  between an oxygen vacancy and  $RE^{3+}$  dopants as a function of the number of  $RE^{3+}$  dopants coordinating the oxygen vacancy. (RE = Sc, Y, La).

to the simple assumption that the defect association energy consists only of pair-interactions between an oxygen vacancy and  $RE^{3+}$  dopants. In all cases, the defect association energy for plural coordination with  $RE^{3+}$  is above the extrapolated, hatched line in Fig. 2, probably due to dopant–dopant repulsion. The dependence of the defect association energy on the CN is nonlinear, especially obvious in the case of  $Sc^{3+}$  doping. However in all cases the defect association energy varies monotonously with the CN of  $RE^{3+}$  ions, so that the tendency shown in Fig. 1 remains the same: doping with smaller ions stabilizes an oxygen vacancy on NN sites, while doping with larger ions destabilizes it.

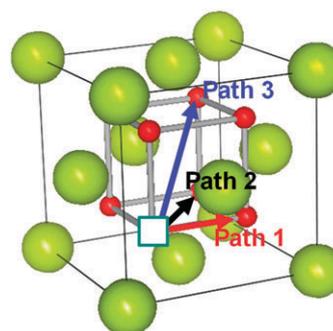
To sum up the defect chemistry of  $RE_2O_3$  doped  $CeO_2$ , our calculations have shown the following results:

- $RE^{3+}$  substitution for  $Ce^{4+}$  leads preferentially to the formation of oxygen vacancies,
- $RE^{3+}$  dopants smaller than  $Gd^{3+}$  tend to trap the oxygen vacancy at the NN site strongly, while  $RE^{3+}$  dopants larger than  $Gd^{3+}$  repel the oxygen vacancy from NN sites.

## 4. Results: oxygen ion migration

### 4.1 Pure $CeO_2$

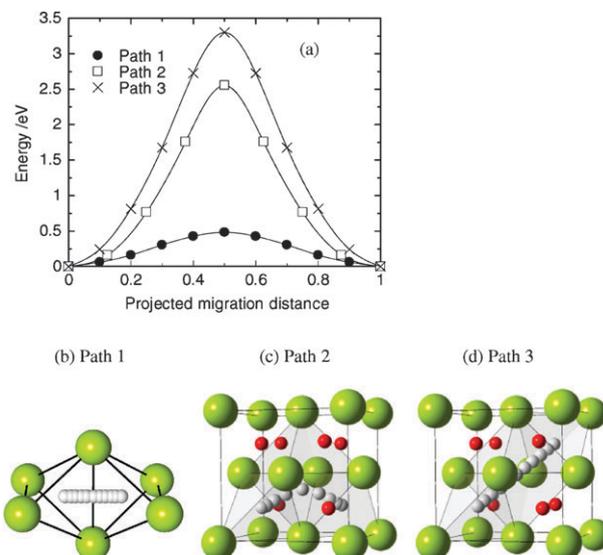
Fig. 3 shows three conceivable migration pathways (Paths 1–3) for oxide ions between adjacent tetrahedral sites in  $CeO_2$ , corresponding to an opposite oxygen vacancy hopping along the  $\langle 100 \rangle$ ,  $\langle 110 \rangle$  and  $\langle 111 \rangle$  direction, respectively. If one considers straightforward hopping, Path 1 requires passing through a dumbbell of two cerium ions in the middle of two adjacent tetrahedral oxygen sites. In this case, the minimum interatomic distance between the hopping oxide ion and the cerium ions is  $\sim 1.95$  Å. Therefore, strong Coulombic attraction and large steric repulsion is expected for Path 1. For Path 3, the oxide ion hops *via* a large interstitial space (4b site) which is coordinated by eight oxide ions with a



**Fig. 3** Three possible oxide ion migration pathways (Path 1–3) in the fluorite structure of ceria. Large light green spheres indicate cerium, the white square indicates an oxygen vacancy and small red spheres correspond to oxide ions.

distance of  $\sim 2.38$  Å, so that local electrostatic repulsion by surrounding anions may prevent the oxide ion from hopping along Path 3. Path 2 may be a moderate situation with a smaller CN of oxygen ions and a larger distance from cations except for one closest  $Ce^{4+}$ .

Fig. 4 presents the computational results of the energy profiles (a) and the corresponding trajectories (b)–(d) for the above three types of jumps obtained by the NEB approach. Note that the horizontal axis in Fig. 4a refers to the jumping ‘oxygen vacancy’, and the projected migration distance indicates its position projected onto the straight line connecting the initial (refers to 0) and final (refers to 1) oxygen vacancy positions. All the energy profiles show a maximum at the middle between the initial and final positions. Obviously, the activation energies of Paths 2 and 3 are much larger than that of Path 1 ( $\sim 0.5$  eV), so that a negligible contribution to the oxygen ionic conductivity is expected for Paths 2 and 3. The oxide ion jumps straightforward for Paths 1 and 3, while



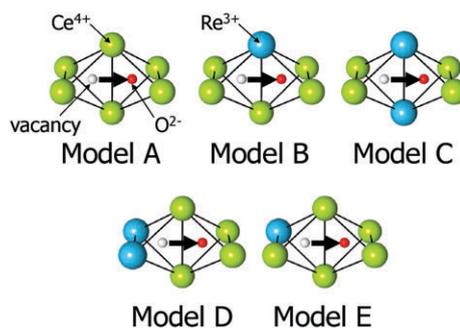
**Fig. 4** (a) Energy profiles during oxide ion hopping for Paths 1–3, and (b)–(d) corresponding trajectories of hopping oxide ions. In (b)–(d), large light-green spheres indicate cerium and small white and red (brighter and darker small) spheres correspond to hopping and non-hopping oxide ions, respectively.

Path 2 shows a curved trajectory passing through the vicinity of interstitial sites being close to the transition point of Path 3. As a result, the activation energies of paths 2 and 3 are both relatively large.

Referring to a previous report by Wang *et al.*,<sup>40</sup> the migration enthalpy for pure CeO<sub>2</sub> would be around 0.6 eV. Fabor *et al.* also reported the migration enthalpy of doped ceria to be 0.5 eV using NMR techniques.<sup>41</sup> Thus, the present computational results for Path 1 show quantitative accordance with the experimental results, supporting the validity of the present results. Moreover, the present computational results regarding the trajectories of oxide ion migration agree in essence with the results of previous studies. For example, Shimojo *et al.* used molecular dynamics simulations<sup>9</sup> and showed for yttria-doped ZrO<sub>2</sub> with fluorite structure that oxide ions hop dominantly along the  $\langle 100 \rangle$  direction between adjacent tetrahedra formed by the cations (Path 1). More recently, Yashima *et al.* investigated the oxygen migration path in Y<sub>2</sub>O<sub>3</sub> doped CeO<sub>2</sub> using neutron powder diffraction combined with the maximum entropy method.<sup>42</sup> Their results indicate that the oxide ion migrates mainly along the  $\langle 100 \rangle$  direction, in agreement with the results of the present computation (Path 1). However, the experimentally observed migration path is not a straight line as depicted in Fig. 4b, but a curved line. In addition, their results also indicate oxygen ion migration along the  $\langle 110 \rangle$  direction (Path 2 in this paper). We believe, however, that the curved pathway for Path 1 and the observed oxide ion migration along Path 2 may be related to the very high temperature of 1434 °C in these experiments. As we are interested in oxygen ion conduction at much lower temperatures we will neglect, hereinafter in this paper, the contribution of conduction pathways 2 and 3 due to their much larger activation energies for oxygen ion jumps.

## 4.2 RE<sub>2</sub>O<sub>3</sub>-doped CeO<sub>2</sub>

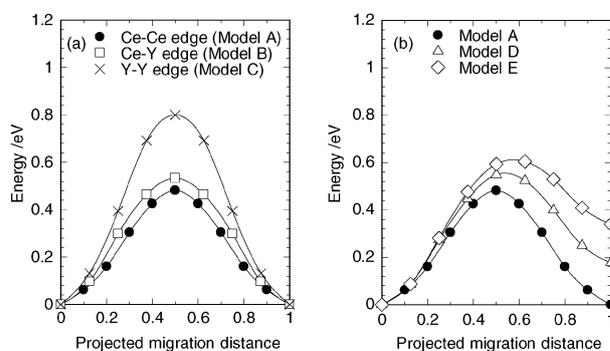
In this section, the effect of RE<sup>3+</sup>-doping on the oxide ion jumps is investigated. We assume that only RE<sup>3+</sup>-ions on nearest neighbour positions (NN-RE<sup>3+</sup>) affect the oxide ion hopping, since in section 3.2 it was found that defect association between a RE<sup>3+</sup>-dopant and an oxygen vacancy is especially significant if both occupy NN positions. However, even with this constraint there are numerous configurational degrees of freedom, which makes it difficult to perform computations by first-principles DFT for all conceivable arrangements of oxygen vacancies and dopants. Thus, from now on we consider dopant–vacancy interactions only within the two adjacent tetrahedra that are defined by Path 1 (see Fig. 4(b)). In this case, the energy profile during the jump of an oxide ion from one specific site to an adjacent specific site depends only on the cation configuration in the two adjacent tetrahedra (see Fig. 5a). Before the jump, the oxide ions resides in a tetrahedral site, and there are five possible cation configurations depending on the coordination number of RE ions; namely O<sub>Ce,Ce,Ce,Ce</sub>, O<sub>Ce,Ce,Ce,RE</sub>, O<sub>Ce,Ce,RE,RE</sub>, O<sub>Ce,RE,RE,RE</sub>, and O<sub>RE,RE,RE,RE</sub>. During the jump from one tetrahedron to another, the oxygen ion has to cross their common edge that could be a Ce–Ce, a Ce–RE, or a RE–RE edge. After the jump, there are again five possible cation configurations in the



**Fig. 5** Five types of nearest neighbour (NN) cation configurations for oxygen vacancy hopping models examined in this study in RE<sup>3+</sup> substituted ceria. The smaller red and white (darker and brighter small) spheres represent an oxide ion and a vacancy, and the larger light green and light blue (brighter and darker large) spheres indicate Ce<sup>4+</sup> and RE<sup>3+</sup>, respectively. Note that the projected migration distance refers to the oxygen vacancy position.

second tetrahedron. As the two tetrahedra share a common edge, there are only 30 distinguishable types of oxide ion jumps.<sup>9</sup> Due to the limitations of computational resources, we chose five important hopping models (Model A–E shown in Fig. 5) for the following reasons. (Note that Model A is exactly the same as considered previously for Path 1 in Fig. 3.) Models A, B and C differ by the number of dopants in the shared edge that has to be crossed by the jumping oxygen ion (Ce–Ce, Ce–RE, RE–RE). However, in all three models the configuration of the oxygen vacancy and the RE<sup>3+</sup>-dopants before and after the jump remains unchanged, which means that in these symmetric cases the corresponding association energies remain unchanged. On the other hand, models D and E reflect the asymmetric effect of defect association, since the coordination number of RE-dopants with oxide ions is different before and after the jump. In model D one “bond” between the oxygen vacancy and the RE<sup>3+</sup>-dopant is broken, in model E two “bonds” are broken.

At first, yttrium was chosen as typical trivalent dopant. The above 5 jump models were evaluated and the results are shown in Fig. 6. The energy profiles corresponding to oxide ion jumps for models A–C (Fig. 6a) exhibit the maximum at the middle between the two adjacent tetrahedral sites as in the case of pure CeO<sub>2</sub> in Fig. 3. Obviously, the Y<sup>3+</sup> occupation at the

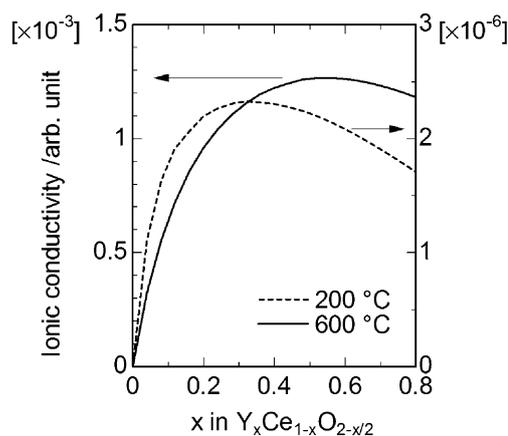


**Fig. 6** Energy profiles for Models A–E (see Fig. 5) in yttria doped ceria. Note that the projected migration distance refers to the ‘oxygen vacancy’ position.

shared-edge sites causes an increase in the activation energy. This increase is no linear function of the number of  $Y^{3+}$  ions: a single Y-ion in the edge increases the migration energy by 0.05 eV (model B) while two Y-ions cause an increase of 0.30 eV (model C). As is the case of Models B and C, Models D and E show a change in the activation energy due to the Y occupation in the first tetrahedron (Fig. 6b). However, the obtained energy profiles are asymmetric, demonstrating that the oxygen vacancy prefers to be located on a NN-position of the  $Y^{3+}$ -dopant (*vice versa* for the oxide ion). Note that the energy differences between the two oxygen sites correspond to the difference of the defect association energies between an oxygen vacancy and one (or two)  $Y^{3+}$ -ion(s) on NN- and on NNN-sites (see also Fig. 1). The increase of the activation energy is almost linear against the number of  $Y^{3+}$ -ions as can be seen in Fig. 6. This can be ascribed to the fact that the defect association energy showed an almost linear behaviour as a function of the number of NN  $Y^{3+}$ -ions (see Fig. 2 for  $CN \leq 2$  and  $RE = Y$ ). Thus, there seems to be a simple relationship between the defect association energy and the activation energy for oxygen ion jumps. Here, we propose a simple model where the activation energy  $E_A$  for oxide ion jumps between two adjacent tetrahedra with different cation configurations can be decomposed into two contributions,  $E_A = \Delta E_{\text{edge}} - (N_{\text{RE}}^{\text{NN}} \Delta E_{\text{RE-V}}^{\text{NN}} + N_{\text{RE}}^{\text{NNN}} \Delta E_{\text{RE-V}}^{\text{NNN}})$ . Here  $\Delta E_{\text{edge}}$  depends only on the cation pair forming the shared-edge of the two adjacent tetrahedra and corresponds to the activation energies of models A, B and C (see Fig. 6(a)).  $N_{\text{RE}}$  is the CN of the oxygen vacancy with RE (except for RE at shared-edge sites), and  $\Delta E_{\text{RE-V}}$  indicates the defect association energy as mentioned above. Using this simple equation, one can obtain the activation energies for forward and backward oxide ion jumps for arbitrary configurations of  $Ce^{4+}$ - and  $RE^{3+}$ -cations only by calculating Models A–C and the defect association energies  $\Delta E_{\text{RE-V}}^{\text{NN}}$  and  $\Delta E_{\text{RE-V}}^{\text{NNN}}$ . Table 4 compares the activation energies for forward and backward jumps predicted by the above method with the exact results from the first-principles study. The predicted activation energies show good accordance with the first-principles results (energy difference is less than 40 meV). This prediction method for the jump activation energy would be beneficial for calculating the macroscopic ionic conduction behaviour. To demonstrate, we calculated the conductivity behaviour using a model that was proposed in a previous report.<sup>16</sup> This model considers the

**Table 4** Activation energies for oxygen vacancy jumps between adjacent tetrahedral sites in Y-doped ceria. Forward jump indicates an oxygen vacancy jump from left to right in Fig. 5, and backward jump indicates the reverse jump

Jump type	Activation energy/eV		Activation energy/eV	
	(First-principles DFT and NEB)		(Prediction according to main text)	
	Forward jump	Backward jump	Forward jump	Backward jump
Model A	0.482		N/A	N/A
Model B	0.533		N/A	N/A
Model C	0.800		N/A	N/A
Model D	0.549	0.372	0.563	0.386
Model E	0.604	0.264	0.643	0.289

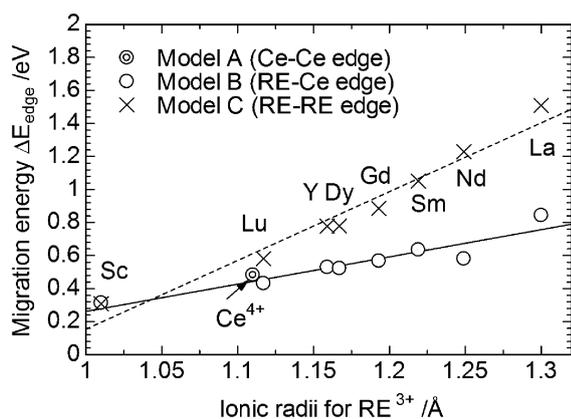


**Fig. 7** Calculated ionic conductivity of  $Y_xCe_{1-x}O_{2-x/2}$  as a function of composition  $x$ . The results were obtained using the conductivity model reported in ref. 30 and taking the activation energies calculated in this study.

oxygen vacancy distribution using mass action equations and jump frequencies using activation energies for the considered configurations of tetrahedra. However, this model<sup>16</sup> considers only NN interactions and assumes a constant attempt frequency (related to the vibrational properties) for oxygen vacancy jumps which is independent of the local cation configuration and temperature. Therefore, the simulated ionic conductivities are compared only on a relative scale. Fig. 7 shows the predicted ionic conductivity behaviour at 200 and 600 °C as a function of composition  $x$  in  $Y_xCe_{1-x}O_{2-x/2}$ . The optimized composition,  $x_{\text{opt}}$ , for ionic conductivity is located around  $x \sim 0.16$  and  $0.28$  at 200 and 600 °C, respectively. Both predicted results overestimate the optimized compositions against experimental results ( $x_{\text{opt}} \sim 0.08$  and  $\sim 0.12$  at 455 and 833 K, respectively<sup>43</sup>). However, the present predictions capture two important features, (i) the existence of optimized compositions, and (ii) these optimized compositions shift to larger values by increasing the temperature. The deviation between predicted and experimental values may arise from disregarding both the NNN site contribution and the repulsive vacancy–vacancy interactions in the conductivity model.<sup>16</sup> Similarly, the present predictions also showed increase of the averaged activation energies with the composition  $x$ , showing qualitative accordance with experimental results at  $x > \sim 0.04$ .<sup>41</sup> We will modify the model and discuss it comprehensively in the near future.<sup>44</sup>

In addition, the above scheme would apply to various  $RE^{3+}$  dopants as well as  $Y^{3+}$  doping. However, we note that smaller  $RE^{3+}$  dopants (such as  $Sc^{3+}$ ) show a nonlinear dependence of the defect association energies on the CN (see Fig. 2), so that linear extrapolation from Model D to Model E is not appropriate.

Finally we consider in Fig. 8 the obtained energy barrier  $\Delta E_{\text{edge}}$  (or the jump activation energies of Models B and C) for various RE dopants as a function of their ionic radii.<sup>38</sup> The energy barrier for pure  $CeO_2$  (Model A) is also plotted for comparison purpose.  $\Delta E_{\text{edge}}$  increases with the ionic radius of  $RE^{3+}$  and is larger for Model C (RE–RE edge) than for Model B (RE–Ce edge) for all RE-dopants, except for Sc where both



**Fig. 8** Calculated migration energies  $\Delta E_{\text{edge}}$  for oxygen ion jumps in Models A, B and C for  $\text{RE}_2\text{O}_3$  doped  $\text{CeO}_2$  as a function of the ionic radii.

values are about the same.<sup>39</sup> The slope for Model C is steeper than that for Model B. The above tendency shows good accordance with first-principles DFT studies by Andersson *et al.*,<sup>11</sup> especially for Model C (RE–RE edge) due to the consistence of the structural models in both computations. On the other hand, it is difficult to compare their results directly with Model A (Ce–Ce edge) and Model B (Ce–RE edge), since they calculated the migration barrier energies using one specific Ce/RE/O/vacancy configuration, which essentially contains NN and NNN defect association energies and asymmetric effects as mentioned before.

We infer that the larger activation energy in Model C may be ascribed to the Coulombic interactions, since smaller attractive interactions are expected at the transition state of Model C ( $\text{RE}^{3+}\text{--O}^{2-}\text{--RE}^{3+}$ ) than for Model B ( $\text{Ce}^{4+}\text{--O}^{2-}\text{--RE}^{3+}$ ). In this respect, the larger migration barrier for doping with larger  $\text{RE}^{3+}$  ions could also be explained by the smaller Coulombic interaction because of the larger interatomic distance between the dopant and the oxygen vacancy. Accordingly, the present results show that improvement of the oxide ionic conductivity can be achieved by using smaller  $\text{RE}^{3+}$  doping in terms of the migration barrier  $\Delta E_{\text{edge}}$ . On the other hand, smaller dopants cause strong binding of the vacancy. Further investigations are needed to reveal the original reasons for the tendency shown in Fig. 8.

## 5. Summary

Atomistic level studies on defect chemistry and oxygen migration in  $\text{Re}_2\text{O}_3$  doped  $\text{CeO}_2$  have been conducted using first-principles DFT. The results show that the dominant point defects are oxygen vacancies charge compensating the aliovalent  $\text{RE}^{3+}$  dopants. Oxide ion (or oxygen vacancy) hops occur straightforward along the  $\langle 001 \rangle$  directions connecting two NN oxygen sites. Defect association effects are non-negligible between  $\text{RE}^{3+}$  ions and oxygen vacancies. The obtained defect association energies show that smaller  $\text{RE}^{3+}$  ions strongly trap oxygen vacancies, while larger  $\text{RE}^{3+}$  ions repel them. Moreover, the energy barrier for oxide ion hopping is a strong function of the ionic radius of the  $\text{RE}^{3+}$  ions which are located at the shared edge of two adjacent

tetrahedra. Increase of  $\text{RE}^{3+}$  ions causes a reduction of the hopping energy barrier, and *vice versa*. Hence, the following trade-off relationship is found: (1) the reduction of the energy barrier by doping with smaller  $\text{RE}^{3+}$  would be accompanied by trapping of an oxygen vacancy at the NN sites of the dopant, whereas (2) doping with larger  $\text{RE}^{3+}$  decreases the trapping effect of oxygen vacancies but increases the energy barrier. Thus—depending on the relative magnitude of the effects—both an increase and a decrease of ionic conductivity are possible. (In the latter situation, larger  $\text{RE}^{3+}$  ions prevent defect association, so that the reduction of the conductivity may be due to the decrease of the effective volume for conduction space.) Such a relationship may account for the previous experimental results that the ionic conductivity showed a maximum for the dopants with intermediate ionic radii.<sup>3,4</sup> Our results were obtained from 5 specific local models for oxygen vacancy jumps where only NN cation arrangements were considered (see Fig. 5). We believe, however, that the DFT energies based on these limited configurations can be extended to approximate the energies for more complex configurations, following the same strategy that was used to get the results in Table 4. Then it should be possible to consider also extreme situations such as (1) a random distribution of dopants and (2) an ordered distribution of dopants. Finally, to understand further why the defect association energy and migration energy strongly depend on the ionic radii of the dopant ions, we will discuss the local structural modifications around defects and in the transition states of hopping ions in the near future.

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